NSN 5961-01-424-6319

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Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-424-6319 **Inclosure Material:** Metal **Overall Length:** 0.115 inches **Overall Height:** 0.092 inches **Overall Width:** 0.062 inches **Function For Which Designed:** Phototransistor **Internal Configuration:** Junction contact **Mounting Method:** Press fit **Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 50.0 breakdown voltage, collector-to-emitter, base open and 7.0 breakdown voltage, emitter to collector, base open **Power Rating Per Characteristic:** 50.0 milliwatts small-signal input power, common-collector preset **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: npn **Terminal Type And Quantity:** 1 case and 1 tab, solder lug Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: